

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application. Please cancel claims 14 and 23, and amend claims 1, 15-17, 24, 26, and 27 as follows:

Listing of Claims:

1. (Currently Amended) A system in package (SiP) device, comprising:
  - a first semiconductor device and an opposing second semiconductor device spaced apart from the first semiconductor device;
  - a dielectric layer interposed between the first semiconductor device and the second semiconductor device;
  - a first conductive pad positioned in the first semiconductor device; and
  - a second conductive pad positioned in the second semiconductor device and configured to capacitively communicate signals from the second semiconductor device to the first semiconductor device; and [[.]]
    - a guard ring coupled to a ground potential and positioned adjacent to at least one of the first conductive pad and the second conductive pad.
2. (Original) The system in package (SiP) device of claim 1, wherein the first conductive pad and the second conductive pad are positioned proximate to the dielectric layer.
3. (Original) The system in package (SiP) device of claim 2, wherein the first conductive pad and the second conductive pad substantially abut the dielectric layer.
4. (Original) The system in package (SiP) device of claim 1, wherein the first conductive pad and the second conductive pad are positioned in the respective first and second devices so that the first conductive pad and the second conductive pad are approximately mutually in alignment.

5. (Original) The system in package (SiP) device of claim 1, further comprising a transmitter coupled to the first conductive pad and a receiver coupled to second conductive pad.

6. (Original) The system in package (SiP) device of claim 5, wherein at least one of the transmitter and the receiver are positioned laterally adjacent to the respective first conductive pad and the second conductive pad.

7. (Original) The system in package (SiP) device of claim 5, wherein at least one of the transmitter and the receiver are positioned beneath the respective first conductive pad and the second conductive pad.

8. (Original) The system in package (SiP) device of claim 1, wherein the first conductive pad and the second conductive pad are comprised of a metal.

9. (Original) The system in package (SiP) device of claim 8, wherein the metal comprises copper.

10. (Original) The system in package (SiP) device of claim 8, wherein the metal comprises aluminum.

11. (Original) The system in package (SiP) device of claim 1, wherein the first conductive pad and the second conductive pad are comprised of polysilicon.

12. (Original) The system in package (SiP) device of claim 1, wherein the dielectric layer comprises silicon dioxide.

13. (Original) The system in package (SiP) device of claim 1, wherein the dielectric layer comprises silicon nitride.

14. (Canceled)

15. (Currently Amended) The system in package (SiP) device of claim 1[[4,]] wherein the guard ring substantially circumferentially encloses at least one of the first conductive pad and the second conductive pad.

16. (Currently Amended) The system in package (SiP) device of claim 1[[4]], further comprising a ground plane positioned adjacent to at least one of the first conductive pad and the second conductive pad, wherein the guard ring is coupled to the ground plane.

17. (Currently Amended) A system in package (SiP) device, comprising:

- a first semiconductor device having a first conductive signal pad positioned adjacent to a first surface;
- a second semiconductor device having a second conductive signal pad positioned adjacent to an opposing second surface, the first surface being spaced apart from the second surface by a dielectric layer, the first conductive signal pad and the second conductive pad being substantially adjacent to each other to capacitively communicate signals between the first semiconductor device and the second semiconductor device; and[[.]]
- a guard ring coupled to a ground potential and positioned adjacent to at least one of the first conductive signal pad and the second conductive signal pad.

18. (Original) The system in package (SiP) device of claim 17, further comprising a transmitter coupled to the first conductive signal pad and a receiver coupled to second conductive signal pad.

19. (Original) The system in package (SiP) device of claim 18, wherein at least one of the transmitter and the receiver are positioned laterally adjacent to the respective first conductive signal pad and the second conductive signal pad.

20. (Original) The system in package (SiP) device of claim 18, wherein at least one of the transmitter and the receiver are positioned beneath the respective first conductive pad and the second conductive pad.

21. (Original) The system in package (SiP) device of claim 17, wherein the first conductive signal pad and the second conductive signal pad have a width of approximately about 30  $\mu\text{m}$ .

22. (Original) The system in package (SiP) device of claim 17, wherein the first conductive signal pad and the second conductive signal pad have a thickness of approximately about 0.85  $\mu\text{m}$ .

23. (Canceled)

24. (Currently Amended) The system in package (SiP) device of claim 17[[23]], wherein the guard ring is laterally spaced apart from the first conductive signal pad and the second conductive signal pad by approximately about 2  $\mu\text{m}$ .

25. (Original) The system in package (SiP) device of claim 24, wherein the guard ring has a lateral width of approximately about 2  $\mu\text{m}$ .

26. (Currently Amended) The system in package (SiP) device of claim 17[[23]], wherein the guard ring is circumferentially disposed about the first conductive signal pad and the second conductive signal pad.

27. (Currently Amended) The system in package (SiP) device of claim 17[[23]], further comprising a ground plane coupled to the guard ring.

28. (Original) The system in package (SiP) device of claim 27, wherein the ground plane is spaced apart from the guard ring by approximately about 1.9  $\mu\text{m}$ .

29-53. (Canceled)